





#### TSSOP-8

#### Pin Definition:

8 1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2 4. Gate 1 5. Gate 2

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
20	22 @ V <sub>GS</sub> = 4.5V	6.5
20	29 @ V <sub>GS</sub> = 2.5V	5.5

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

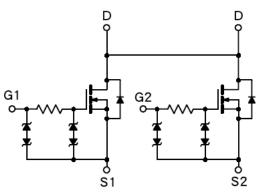
### **Application**

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

#### **Ordering Information**

Part No.	Package	Packing
TSM6968DCA RV	TSSOP-8	3Kpcs / 13" Reel

#### **Block Diagram**



**Dual N-Channel MOSFET** 

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		$V_{GS}$	±12	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V.		I <sub>D</sub>	6.5	А	
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	30	А	
Continuous Source Current (Diode Cond	Diode Conduction) <sup>a,b</sup> I <sub>S</sub> 1.4		1.4	А	
Maximum Dawar Dissination	Ta = 25°C	В	1.04	W	
Maximum Power Dissipation	Ta = 75°C	P <sub>D</sub>	0.625		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	$R\Theta_{JF}$	83	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ <sub>JA</sub>	120	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.





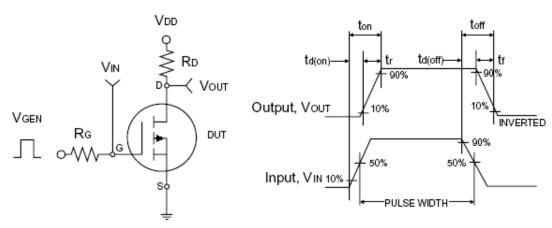
### 20V Dual N-Channel MOSFET w/ESD Protected

### **Electrical Specifications** (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	8.0	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6.0A$	В		15	22	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.0A$	R <sub>DS(ON)</sub>		20	29	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	g <sub>fs</sub>		16		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	$V_{SD}$		0.6	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A,	$Q_g$		15	20	
Gate-Source Charge	, , ,	$Q_gs$		3.4		nC
Gate-Drain Charge	$V_{GS} = 4.5V$ $Q_{gd}$	$Q_{gd}$		1.2		
Input Capacitance	\	C <sub>iss</sub>		950		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		450		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	$C_{rss}$		135		
Switching <sup>c</sup>						
Turn-On Delay Time	V - 40V D - 400	t <sub>d(on)</sub>		140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_{L} = 10\Omega,$ $I_{D} = 1A, V_{GEN} = 4.5V,$ $R_{G} = 6\Omega$	t <sub>r</sub>		210	250	nS
Turn-Off Delay Time		$t_{d(off)}$		3700	4800	113
Turn-Off Fall Time	17G - 022	t <sub>f</sub>		2000	2600	

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

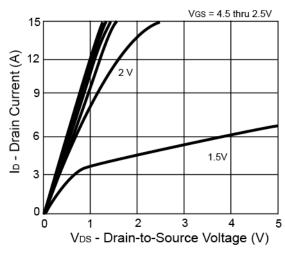




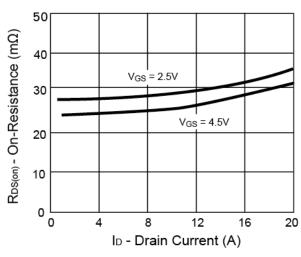


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

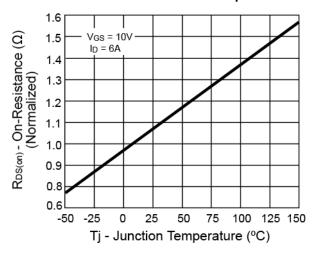




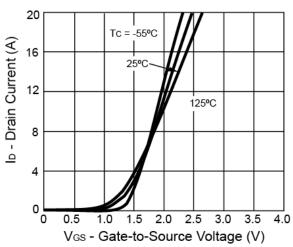
#### On-Resistance vs. Drain Current



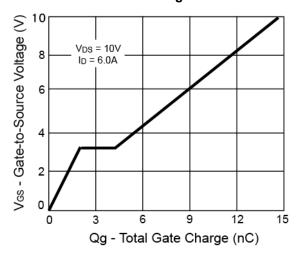
#### On-Resistance vs. Junction Temperature



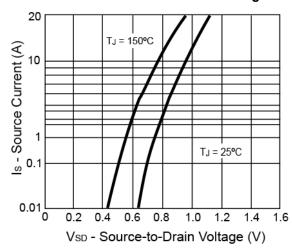
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage









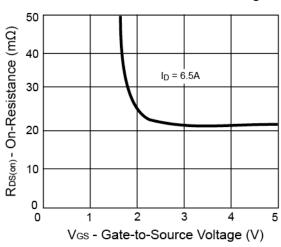
## 20V Dual N-Channel MOSFET w/ESD Protected

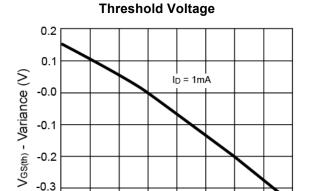
-0.4

-50 -25

#### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage





25

50

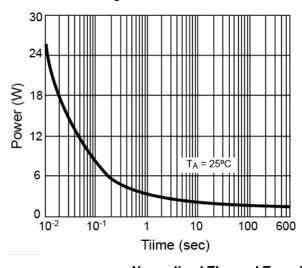
Tj - Junction Temperature (°C)

75

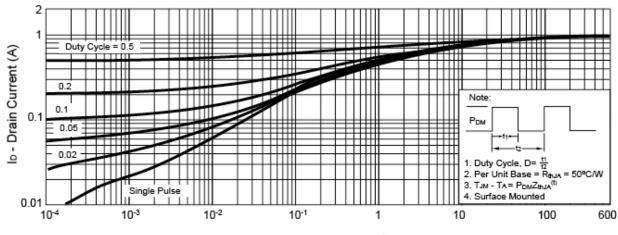
100

125 150

#### Single Pulse Power



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



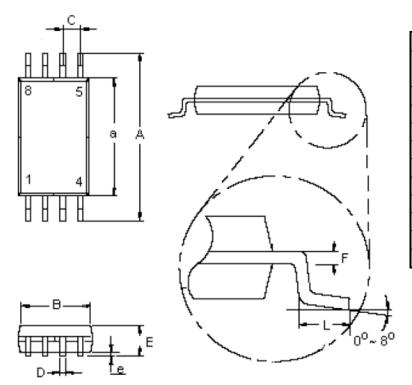
Square Wave Pulse Duration (sec)





### 20V Dual N-Channel MOSFET w/ESD Protected

# **TSSOP-8 Mechanical Drawing**



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



### 20V Dual N-Channel MOSFET w/ESD Protected

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